Serial No.10/769,127 HP Docket No: 200209576-1

REMARKS

This communication is in response to the Office Action dated January 26, 2006. Claims 1-10, 13-20, 22 and 23 are pending in the present Application.

Claims 11, 12, 21 and 24-30 have been withdrawn from consideration. Claims 1-10, 13-20, 22 and 23 are rejected.

§102 Rejections

Claims 1-10, 13-20, 22 and 23

For ease of review, Applicant reproduces independent claims 1 and 13 herein below:

- A method for forming a semiconductor device comprising:
 forming a 3-dimensional (3D) pattern in a substrate; and
 depositing at least one material over the substrate in accordance with
 desired characteristics of the semiconductor device.
- 13. A system for forming a semiconductor device comprising:

 means for forming a 3-dimensional (3D) pattern in a substrate; and

 PAGE 4/4 * RCVD AT 4/26/2006 6:27:57 PM [Eastern Daylight Time] * SVR:USPTO-EFXRF-5/9 * DNIS:2738300 * CSID:408 938 0980 * DURATION (mm-ss):01-26

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